METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING APPARATUS

ABSTRACT

There is provided a technique that includes: forming a film on the substrate by performing a first cycle a predetermined number of times, the first cycle including performing: (a) supplying a first processing gas to the substrate; and (b) supplying a second processing gas to the substrate, wherein (a) includes sequentially performing: (a-1) opening a first storage filled with the first processing gas and supplying the first processing gas discharged from the first storage to the substrate via a first supply port; (a-2) exhausting a processing space in which the substrate is processed while stopping the supply of the first processing gas to the substrate; and (a-3) opening a second storage filled with the first processing gas and supplying the first processing gas discharged from the second storage to the substrate via a second supply port different from the first supply port.

Fig. 4